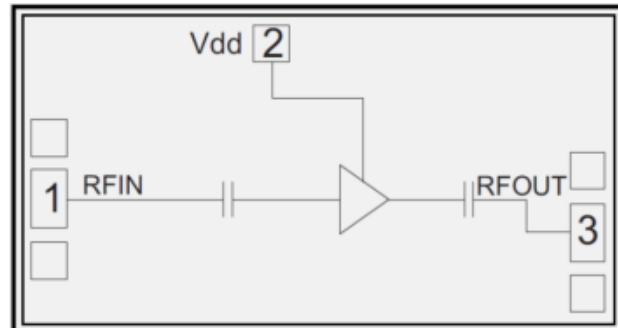


Features

- Frequency: 5-12GHz
- Small Signal Gain: 12.5dB
- Gain Flatness: $\leq \pm 0.5$ dB
- Noise Figure: 2.2dB
- P1dB: 20dBm
- Psat: 21dBm
- Power Supply: +5V/77mA
- Input/Output: 50 Ω
- Die Size: 1.2 x 1.15 x 0.1 mm

Typical Applications

- Test Instrumentation
- Microwave Radio & VSAT
- Military & Space
- Telecom Infrastructure
- Fiber Optics

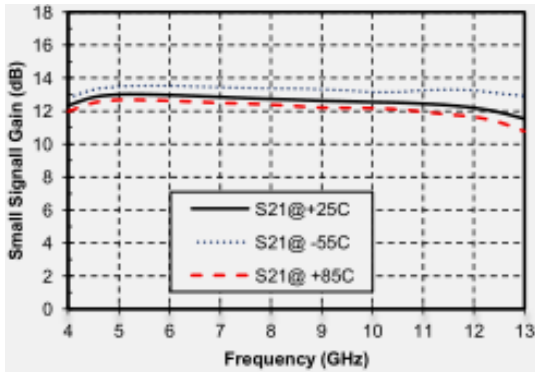
Functional Block Diagram

Electrical Specifications

TA = +25°C, Vd = +5V

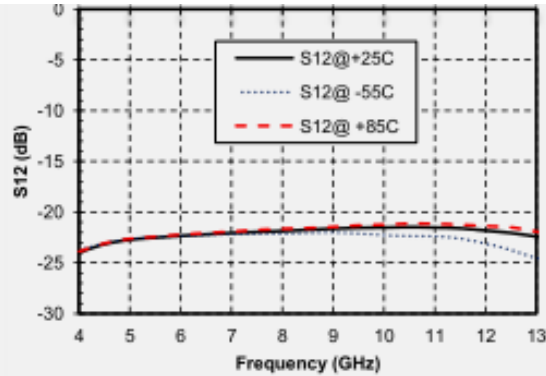
Parameters	Min.	Typ.	Max.	Units
Frequency	5-12			GHz
Small Signal Gain	11.5	12.5	14	dB
Gain Flatness		± 0.5		dB
Noise Figure		2.2		dB
Output 1dB Compression (P1dB)		20		dBm
Saturated Output Power (Psat)		21		dBm
Input Return Loss		17		dB
Output Return Loss		17		dB
Static Current	65	77	90	mA



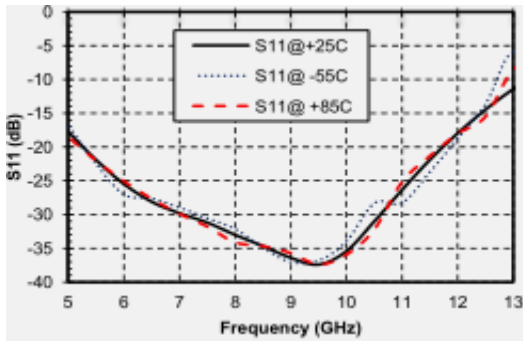
Gain vs. Frequency



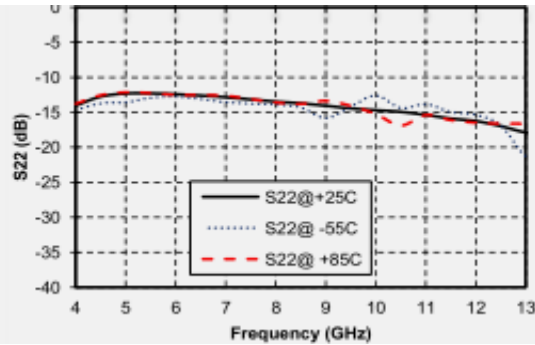
Reverse Isolation & Frequency



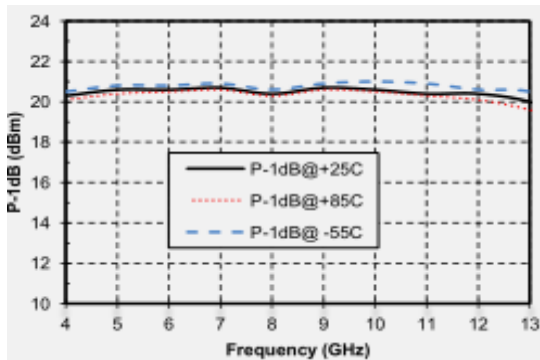
Input Return Loss vs. Frequency



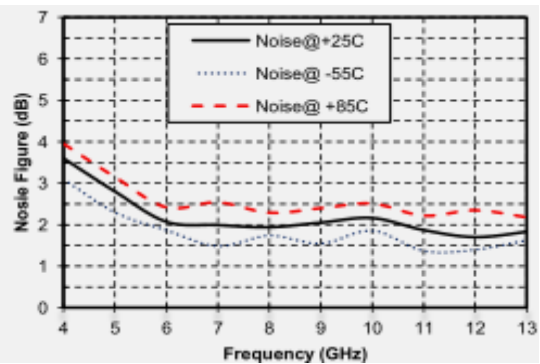
Output Return Loss vs. Frequency



P1dB vs. Frequency

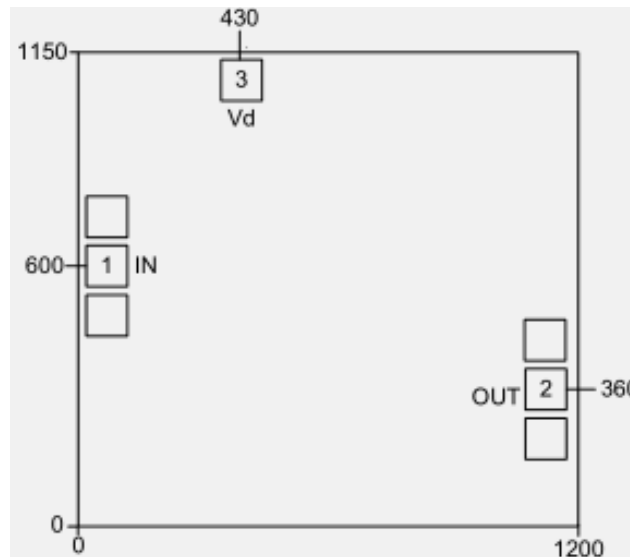


Noise Figure vs. Frequency





Outline Drawing:
All Dimensions in μm

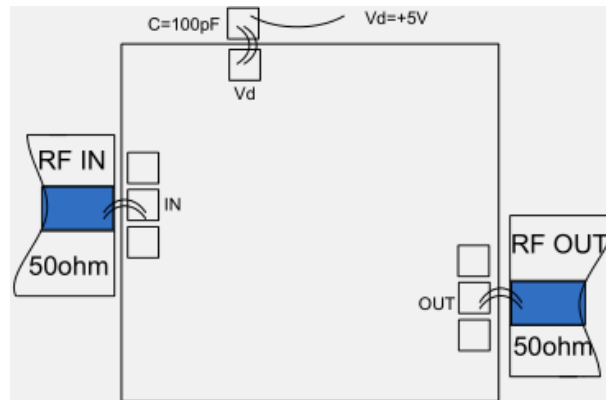


Pad Description

Pad	Function	Description	Equivalent Circuit
1	RF IN	RF signal input terminal; no blocking capacitor required.	
2	RF OUT	RF signal output terminal; no blocking capacitor required.	
3	Vd	Amplifier drain bias; external 100pF bypass capacitor required.	
Die bottom	GND	Die bottom must be connected to RF/DC ground.	



Assembly Drawing



Notes:

1. Die thickness: 100um
2. Typical bond pad is 100*100 μm^2
3. Bond pad metalization: Gold
4. Backside metalization: Gold
5. Backside of the die (GND)
6. No connection required for unlabeled bond pads

Maximum Ratings:

1. Maximum drain voltage: +7V
2. Maximum input power: +20dBm
3. Operating temperature: -55°C to +85°C
4. Storage temperature: -65°C to +150°C